L Number	Hits	Search Text	DB	Time stamp
1	3702	((257/296) or (257/401) or (257/410)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/06 16:38
2	0	(((257/296) or (257/401) or (257/410)).CCLS.) and "bird's beak" near4 gate near4 underneath and silicon adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/06 16:39
-	5	272,968.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/06 16:38
-	1	"5612249".PN.	USPAT	2002/05/22 14:58
-	1	"5637514".PN.	USPAT	2002/05/22 14:59
-	1	"5798550".PN.	USPAT	2002/05/22 14:59
-	1	"6015736".PN.	USPAT	2002/05/22 15:00
-	3	("5306655").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 15:43
-	3	("5360758").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 17:03
-	301	((side adj wall or sidewall or side-wall) adj spacer near6 nitride) and 257/$6.ccls. and (field adj effect adj transistor or fet or mos or mos adj fet or mosfet or nmos or pmos or nmosfet or pmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/23 09:41
-	3	("5382533").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 17:51
-	3	("5679968").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 17:52
-	3	("5714413").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 17:53
-	0	("ep-621632$-$.did.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 17:53
-	0	("ep-621632$-$.did.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 17:53
-	0	rajeevakumar.in. and dram adj cell adj structure	EPO	2002/05/22 17:55
-	6	rajeevakumar.in. and dram adj cell adj structure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 17:55

–	3	("5612249").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/23 10:42
–	0	earom and selection same transistor same dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/23 10:43
–	27	earom and transistor same dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/23 10:44
–	6	earom and transistor same dram.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/23 10:45
–	109394	earom.ti,ab. and dram.ti,ab. and 257/$6.ccls. or 438/$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/23 10:46
–	5	earom.ti,ab. and dram.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/23 10:47
–	187	selection near12 (transistor or fet or mosfet) near12 dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/23 10:49
–	44	(selection near6 (transistor or fet or mosfet) near6 dram) and (257/$6.ccls. or 438/$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/23 12:09
–	3	("5854500").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/23 12:14
–	2	("6037639").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/23 13:57
–	1962	(257/296).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/23 12:26
–	1041	(257/401).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/23 15:08
–	432	(257/410).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/23 15:08
–	2	("5885553").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/06 10:35

-	2	("5612249").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/06 12:04
-	0	(side adj wall or sidewall) near12 gate adj oxide near12 silicon adj nitride adj spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/06 12:06
-	15	(side adj wall or sidewall) near12 gate adj oxide near12 silicon adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/06 12:07
-	147	oxidation adj barrier near4 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/06 13:06
-	201	(MOS or MOSFET).ti,ab,clm. and silicon adj nitride near4 (sidewall or side adj wall) near4 spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/06 13:09